PCN	Num	ber:	2	016	1130000			ı	PCN Da	te:	Dec	5, 2016
Title: Alternate Fab (MIHO8) and Assembly (CDAT) site Qualification					ificatior	s for se	lect o	devices				
Cus	tomer	Contact:		PC	CN Manag	<u>er</u>		I	Dept:		Qua	lity Services
Pro	nosed	1 st Ship Da	ate:	Ma	arch 5, 20	17	Estimated Sa	mp	ole			e provided at
				,			Availability:				sam	ple request.
	nge T			+-	1 1 0 1	1 5		IF				
		nbly Site		╁┝	Assemb					embly N		
	Desig Test S			╁┝			cification ping/Labeling			t Proces		cification
		· Bump Site		╁늗			Material	ļ		fer Bum)CASS
Ħ		Fab Site		╁┝	Wafer			Ť	_	fer Fab		
				TE	Part nu							
							Details					
Des	criptio	on of Chan	ge:									
		Test (CDAT) on difference				:	I in the "Product	Af	fected"			is document.
					Clark AT				CDAT			
Mount Compound						4207768 4207123						
Mold Compound					20625							
	Mo	old Compou	ınd			420	08625			42221	L98	
	Mo	old Compou	ınd			420	08625			42221	L98	
	Mo	•	ind ent Si	tes		420	08625	<u> </u>	Addition	42221		
	urrent	Curro	ent Si	ımp		nfer	Additional		Fab	al Sites	1 p	Wafer Diameter
Fa		Curre	ent Si Bi		Dian					al Sites	np e	Wafer Diameter 200 mm
Test test Qua	urrent b Site RFAB cover MQ.	Fab Process LBC7 age, insertic	Bi S CLA	ump Site RK-E	Dian BP 300	nfer neter mm	Additional Fab Site MIHO8	P	Fab Process LBC7	al Sites Bun Sit	1p e (-BP	Diameter 200 mm
Test test Qua	rrent b Site RFAB cover MQ. I detail	Fab Process LBC7 age, insertions are provided or Change:	Bi S CLA	ump Site RK-E	Dian BP 300	nfer neter mm	Additional Fab Site MIHO8	P	Fab Process LBC7	al Sites Bun Sit	1p e (-BP	Diameter 200 mm
Test test Qua Rea Con	rrent b Site RFAB cover MQ. I detail	Curro Fab Process LBC7 age, insertions as are provided or Change:	Bi CLA	imp Site RK-E ondi	Dian 3P 300 itions will Qual Dat	nfer neter mm remain	Additional Fab Site MIHO8 consistent with	cu	Fab Process LBC7 Irrent te	Bun Sitt CLARK esting an	np e (-BP	Diameter 200 mm
Test test Qua Rea Con	rrent b Site RFAB cover MQ. I detail son for tinuity icipate	Fab Process LBC7 age, insertices are provided impact of Supply	Bi SCLA	mp Site RK-E ondi the	Dian 3P 300 itions will Qual Dat	remain	Additional Fab Site MIHO8 consistent with	cu	Fab Process LBC7 arrent to	Bun Sit CLARK esting ar	np e (-BP nd ve	Diameter 200 mm erified with
Test test Qua Rea Con	rrent b Site RFAB c cover MQ. I detail son fo tinuity icipate	Curro Fab Process LBC7 age, insertions as are provided or Change:	CLA	imp Site RK-E ondi	Pitons will Qual Dat Fit, Function of the production of the prod	remain a Section, (all Declation dat b. Uponed at th	Additional Fab Site MIHO8 consistent with	cu ct case	Fab Process LBC7 Irrent to Contendable follower the re-	Bun Site CLARK esting an obsitive treports lowing to vised residue.	/ ne s are he preports	piameter 200 mm erified with gative): driven from roduction s can be

Changes to product identification resulting from this PCN:

Fab

Chip Sites	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
RFAB	RFB	USA	Richardson

MIHO8	MH8	JPN	Ibaraki
Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City

Assembly Site	Assembly Site Origin (22L)	Assembly Country Code (21L)	Assembly City
Clark AT	QAB	PHL	Angeles City, Pampanga
CDAT	CDA	CHN	Chengdu

Sample product shipping label (not actual product label)





(1P) \$N74L\$07N\$R (Q) 2000 (D) 0336 (31T)LOT: 3959047MLA (4W) TKY(1T) 7523483\$I2 (P) (2P) REV: (Y) 0633317 (20L) C\$0: SHE (21L) CCO: U\$A (22L) ASO: MLA (23L) ACO: MY\$

Topside Device marking (if included):

Assembly site code for QAB= I **Assembly site code for CDA = 8**

Product Affected:

1100007111000001				
BQ25890RTWR	BQ25892RTWT	BQ25895RTWR	BQ25896RTWR	
BQ25890RTWT	BQ25895MRTWR	BQ25895RTWT	BQ25896RTWT	
BQ25892RTWR	BQ25895MRTWT			•



Qualification Report

Qualification of BQ2589XRTW family in CDAT including BQ25890, BQ25892, BQ25895M, and BQ25896RTW using materials from MIHO8/LBC7 Approve Date 07-Nov-2016

Product Attributes

Attributes	Qual Device: BQ25892RTW	Qual Device: BQ25895MRTW	QBS Process Reference: TPS62110RSA	QBS Package Reference: BQ25895MRTW	QBS Package Reference: TPS62140RGTR
Assembly Site	CHENGDU A/T	CHENGDU A/T	CAR	CHENGDU A/T	CHENGDU A/T
Package Family	QFN, 4 x 4 MM	QFN, 4 x 4 MM	QFN	QFN	VQFN
Flammability Rating	-	-	UL 94 V-0	UL 94 V-0	UL 94 V-0
Wafer Fab Supplier	MIHO8	MIHO8	MIHO8	RFAB	MIHO-8
Wafer Fab Process	LBC7	LBC7	LBC7	LBC7X+1UM VIATOP+6DU SEAL	LBC7X

- QBS: Qual By Similarity Qual Device BQ25896RTW is qualified at LEVEL2-260CG
- Qual Device BQ25890RTW is qualified at LEVEL2-260C
- Qual Device BQ25895MRTW is qualified at LEVEL2-260CG
- Qual Device BQ25892RTW is qualified at LEVEL2-260CG

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Туре	Test Name / Condition	Duration	Qual Device: BQ25892RTW	Qual Device: BQ25895MRTW	QBS Process Reference: TPS62110RSA	QBS Package Reference: BQ25895MRTW	QBS Package Reference: TPS62140RGTR
AC	Autoclave 121C	192 Hours	-	-	-	-	3/231/0
AC	Autoclave 121C	96	-	-	-	3/270/0	-
AC	Autoclave 121C	96 Hours	-	-	3/231/0	-	3/231/0
CDM	ESD - CDM	1000 V	1/3/0	1/3/0	-	-	-
ED	Electrical Characterization	(Per Datasheet Parameters)	1/Pass	1/Pass	-	-	-
ED	Electrical Characterization	Per Datasheet Parameters	-	-	-	-	1/Pass
ELFR	Early Life Failure Rate, 140C	48 Hours	-	-	3/1881/0	-	-
HAST	Biased HAST, 130C/85%RH	96 Hours	-	-	3/231/0	-	-
HBM	ESD - HBM	2500 V	1/3/0	1/3/0	-	-	-
HTOL	Life Test, 140C	480 Hours	-	-	3/231/0	-	-
HTSL	High Temp Storage Bake 170C	420 Hours	-	-	3/231/0	3/270/0	-
LU	Latch-up	(per JESD78)	1/6/0	1/6/0	3/15/0	-	-
MSL	Thermal Path Integrity	Level 2-260C	-	-	-	-	3/36/0
TC	Temperature Cycle, - 65/150C	500	-	-	-	3/270/0	-
TC	Temperature Cycle, - 65/150C	500 Cycles	-	-	3/231/0	-	3/231/0
TS	Thermal Shock, - 65/150C	500 Cycles	-	-	3/231/0	-	-
WBP	Bond Pull	76 Wire, 3 units min	-	-	-	-	3/228/0
WBS	Ball Bond Shear	76 balls, 3 units min	-	-	-	-	3/228/0

⁻ Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

Green/Pb-free Status:

Qualified Pb-Free(SMT) and Green

⁻The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours -The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/1k Hours, and 170C/420 Hours

⁻The following are equivalent Temp Cycle options per JESD47: -55C/125C/700 Cycles and -65C/150C/500 Cycles

For questions regarding this notice, e-mails can be sent to the regional contacts shown below, or you can contact your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com
Japan	PCNJapanContact@list.ti.com